Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D T_A = +25°C
30V	1.2Ω @ V_{GS} = 4.5V	440mA
	1.5Ω @ V_{GS} = 2.5V	395mA

Features and Benefits

- N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

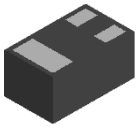
- Load Switch

Mechanical Data

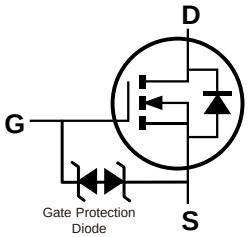
- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.001 grams (Approximate)



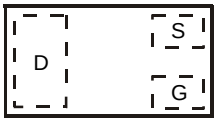
X2-DFN1006-3



Bottom View



Equivalent Circuit



Top View
Pin-Out

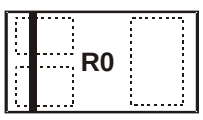
Ordering Information (Note 4)

Part Number	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
DMN32D0LFB4-7B	7	8	10,000

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

DMN32D0LFB4-7B



Top View
Bar Denotes Gate and Source Side

R0 = Product Type Marking Code

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	±10	V
Drain Current (Note 5)	I_D	440	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5) @T_A = +25°C	P_D	350	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	357	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current @ T_C = +25°C	I_{DSS}	—	—	1	µA	V_{DS} = 30V, V_{GS} = 0V
Gate-Body Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±10V, V_{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.6	—	1.2	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	— — —	0.6 0.7 0.8	1.2 1.5 2.2	Ω	V_{GS} = 4.5V, I_D = 100mA V_{GS} = 2.5V, I_D = 20mA V_{GS} = 1.8V, I_D = 20mA
Source-Drain Diode Forward Voltage	V_{SD}	—	0.7	1.4	V	V_{GS} = 0V, I_S = 115mA
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	44.8	—	pF	V_{DS} = 15V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	4.6	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	2.5	—	pF	
Gate Resistance	R_g	—	81.2	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	0.6	—	nC	V_{GS} = 4.5V, V_{DS} = 15V, I_D = 350mA
Gate-Source Charge	Q_{gs}	—	0.1	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.2	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	3.4	—	ns	V_{DD} = 20V, R_L = 250Ω, V_{GEN} = 4.5V, R_{GEN} = 6Ω
Turn-On Rise Time	t_R	—	2.5	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	19	—	ns	
Turn-Off Fall Time	t_F	—	7.9	—	ns	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

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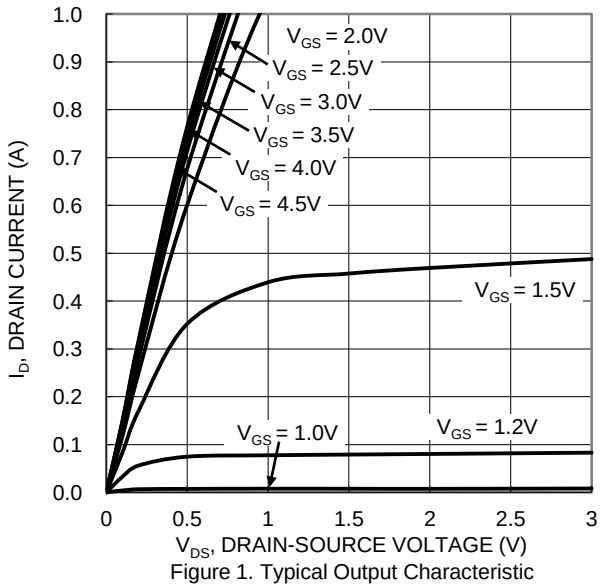


Figure 1. Typical Output Characteristic

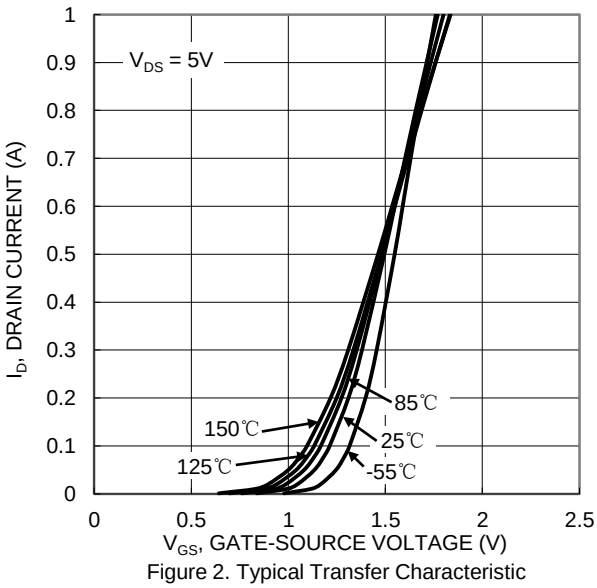


Figure 2. Typical Transfer Characteristic

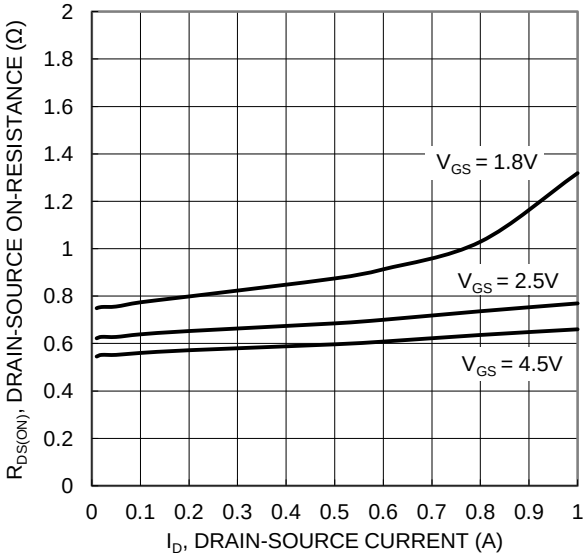


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

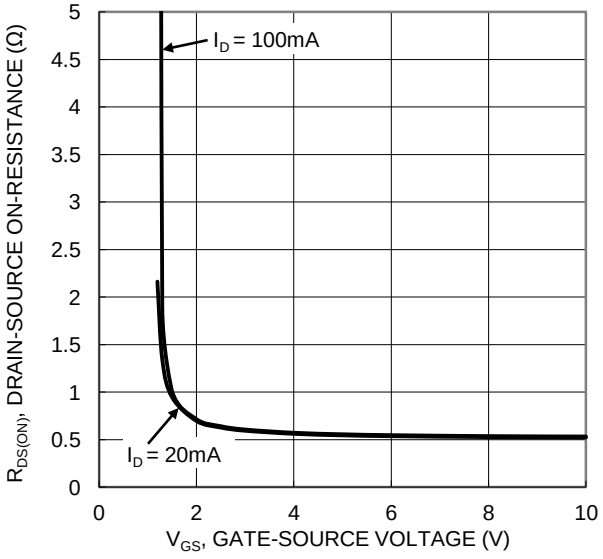


Figure 4. Typical Transfer Characteristic

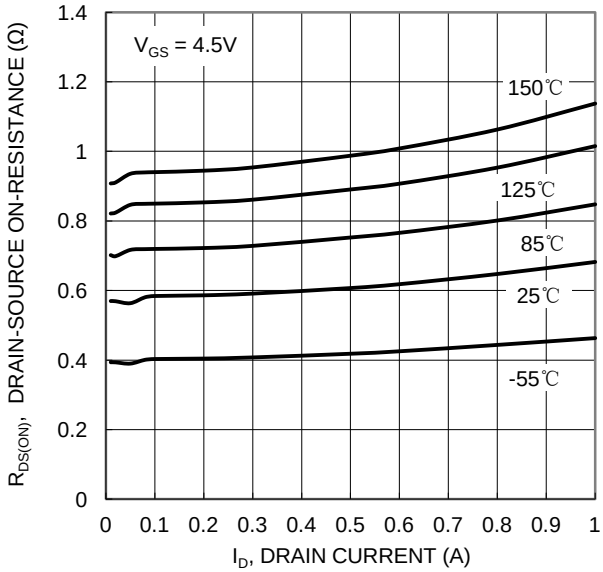


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

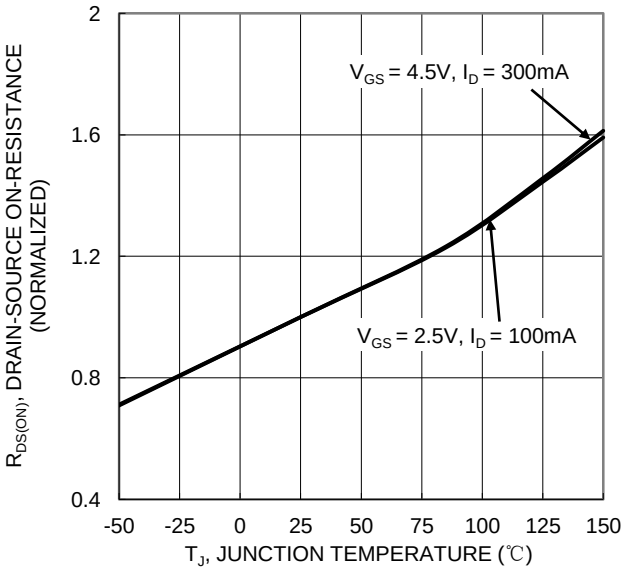


Figure 6. On-Resistance Variation with Temperature

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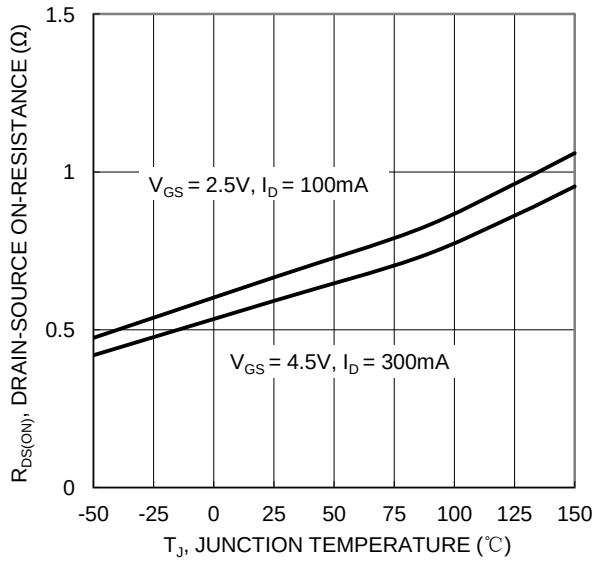


Figure 7. On-Resistance Variation with Temperature

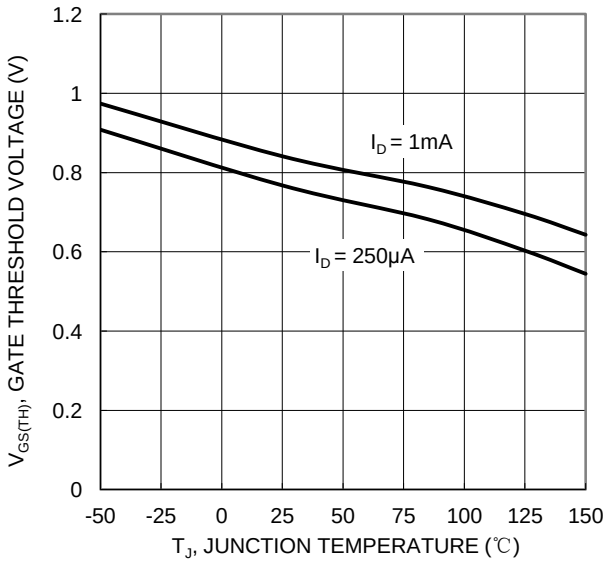


Figure 8. Gate Threshold Variation vs. Junction Temperature

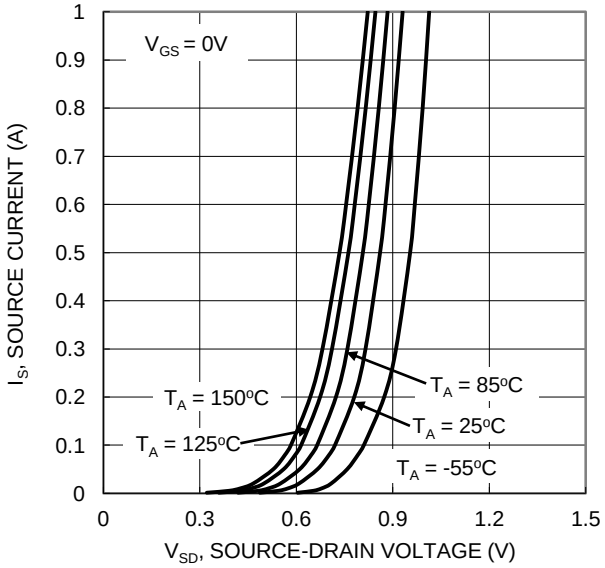


Figure 9. Diode Forward Voltage vs. Current

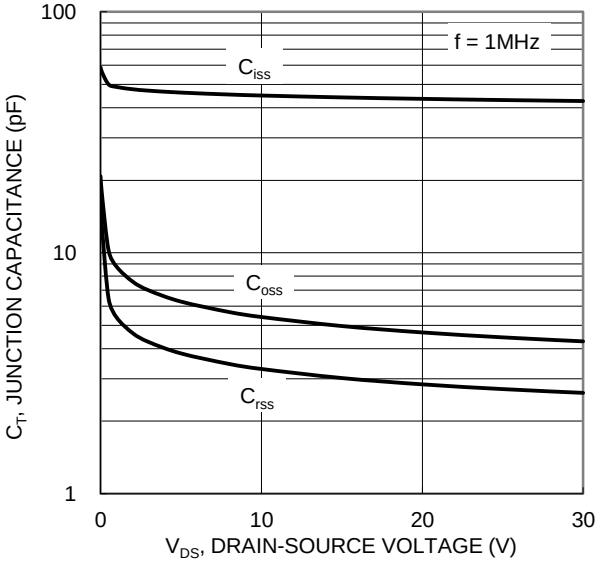


Figure 10. Typical Junction Capacitance

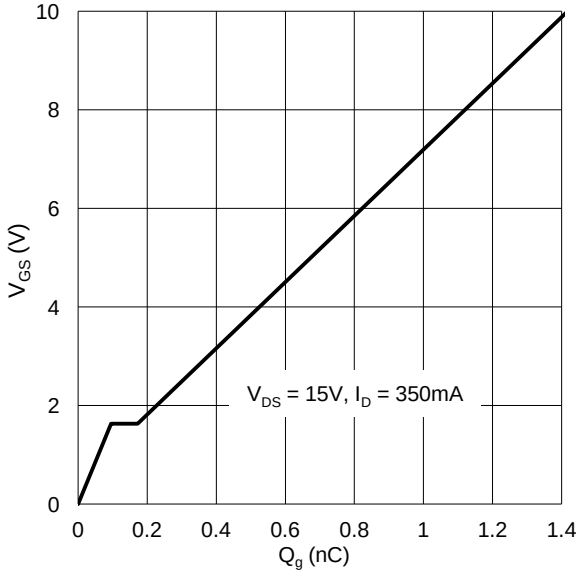


Figure 11. Gate Charge

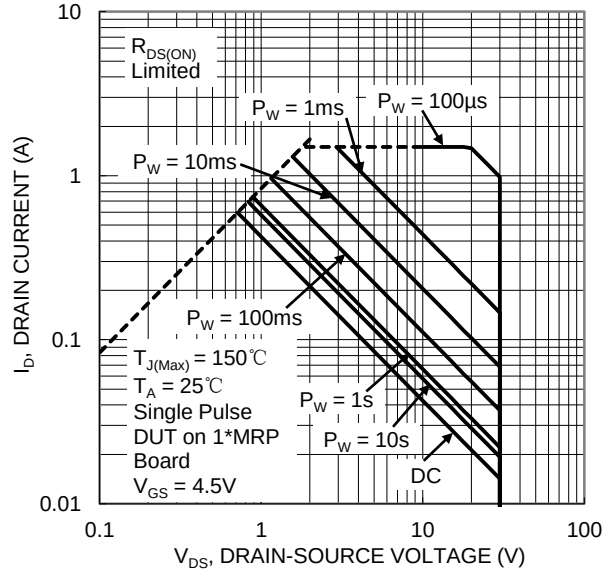


Figure 12. SOA, Safe Operation Area

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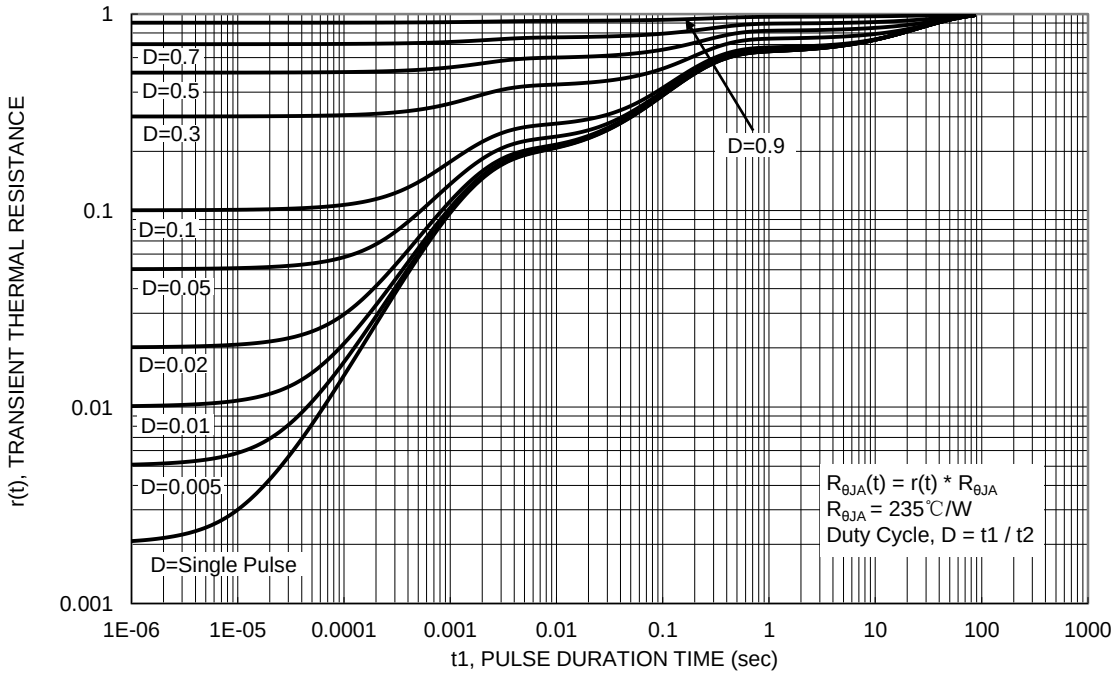


Figure 13. Transient Thermal Resistance

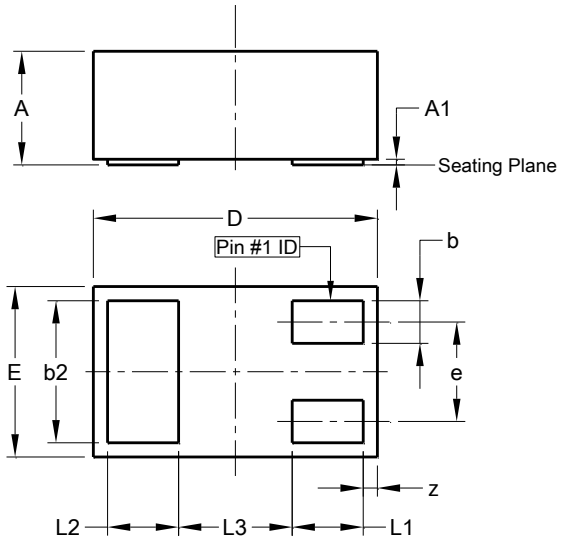
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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1006-3

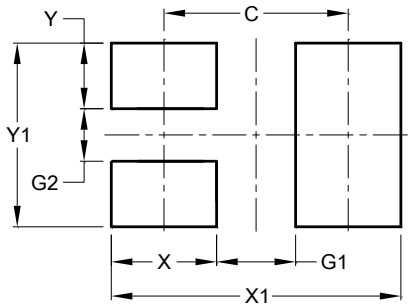


X2-DFN1006-3			
Dim	**Min**	**Max**	**Typ**
A	-	0.40	-
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.05	1.00
E	0.55	0.65	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1006-3



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70

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